

Silicon PNP Power Transistors

2SA758

DESCRIPTION

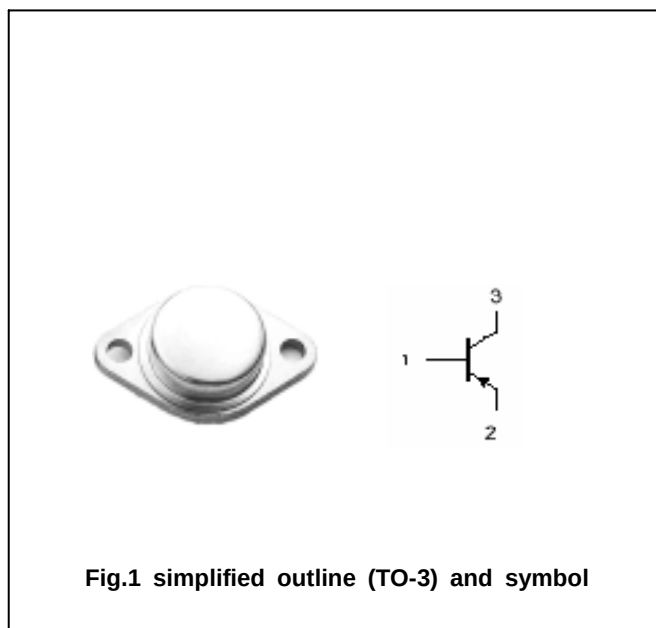
- With TO-3 package
- Complement to type 2SC898

APPLICATIONS

- For 80W audio amplifier power output applications

PINNING(see Fig.2)

PIN	DESCRIPTION
1	Base
2	Emitter
3	Collector

Absolute maximum ratings($T_a=^{\circ}\text{C}$)

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
V_{CBO}	Collector-base voltage	Open emitter	-130	V
V_{CEO}	Collector-emitter voltage	Open base	-110	V
V_{EBO}	Emitter-base voltage	Open collector	-5	V
I_C	Collector current		-7	A
I_{CM}	Collector current-peak		-12	A
P_C	Collector power dissipation	$T_C=25^{\circ}\text{C}$	80	W
T_j	Junction temperature		150	$^{\circ}\text{C}$
T_{stg}	Storage temperature		-55~150	$^{\circ}\text{C}$

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CHARACTERISTICS

T_j=25°C unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
V _{(BR)CEO}	Collector-emitter breakdown voltage	I _C =-50mA ; R _{BE} =∞	-110			V
V _{(BR)CBO}	Collector-base breakdown voltage	I _C =-5mA , I _E =0	-130			V
V _{(BR)EBO}	Emitter-base breakdown voltage	I _E =-5mA , I _C =0	-5			V
V _{CEsat}	Collector-emitter saturation voltage	I _C =-5A; I _B =-1A			-1.8	V
V _{BE}	Base-emitter on voltage	I _C =-1A ; V _{CE} =-5V			-1.5	V
I _{CBO}	Collector cut-off current	V _{CB} =-30V; I _E =0			-1	mA
h _{FE-1}	DC current gain	I _C =-1A ; V _{CE} =-5V	25		200	
h _{FE-2}	DC current gain	I _C =-5A ; V _{CE} =-5V	20			
f _T	Transition frequency	I _C =-1A ; V _{CE} =-5V		20		MHz

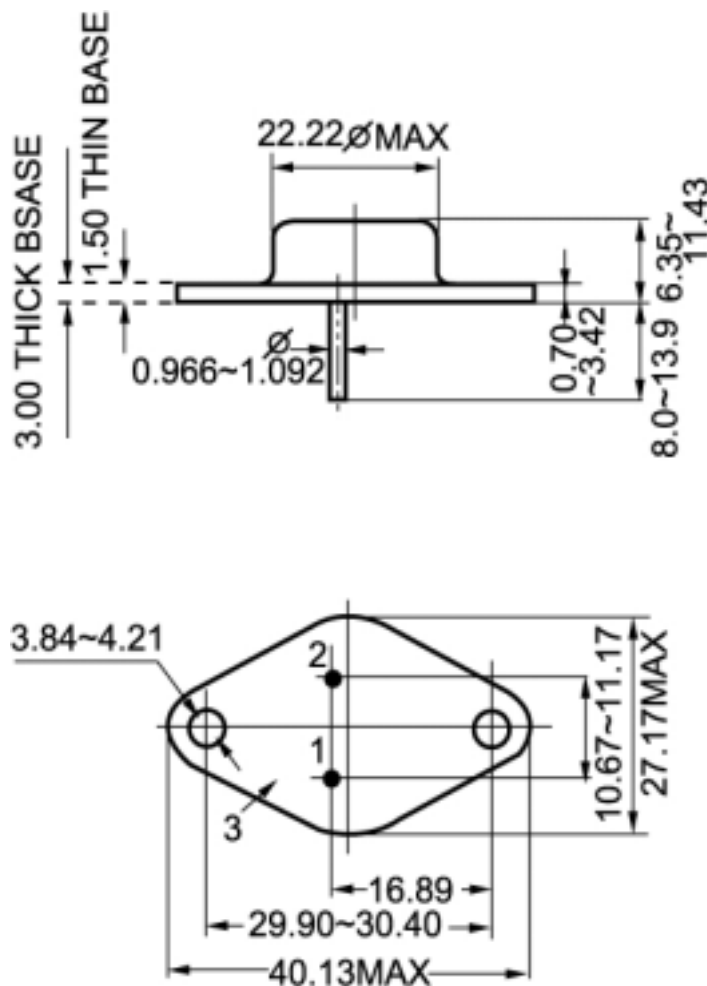
◆ h_{FE-1} Classifications

A	B	C
25-60	50-120	100-200

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PACKAGE OUTLINE

Fig.2 outline dimensions (unindicated tolerance: $\pm 0.1\text{mm}$)